





CDCLVC1102, CDCLVC1103, CDCLVC1104 CDCLVC1106, CDCLVC1108, CDCLVC1110, CDCLVC1112

SCAS895B-MAY 2010-REVISED FEBRUARY 2017

## CDCLVC11xx 3.3-V and 2.5-V LVCMOS High-Performance Clock Buffer Family

#### Features 1

**Fexas** 

Instruments

- High-Performance 1:2, 1:3, 1:4, 1:6, 1:8, 1:10, 1:12 LVCMOS Clock Buffer Family
- Very Low Pin-to-Pin Skew < 50 ps
- Very Low Additive Jitter < 100 fs
- Supply Voltage: 3.3 V or 2.5 V
- $f_{max} = 250 \text{ MHz}$  for 3.3 V  $f_{max} = 180 \text{ MHz}$  for 2.5 V
- Operating Temperature Range: -40°C to 85°C
- Available in 8-, 14-, 16-, 20-, 24-Pin TSSOP Package (All Pin-Compatible)

### 2 Applications

General-Purpose Communication, Industrial, and **Consumer Applications** 

### 3 Description

Tools &

The CDCLVC11xx is a modular, high-performance, low-skew, general-purpose clock buffer family from Texas Instruments.

The entire family is designed with a modular approach in mind. It is intended to round up TI's series of LVCMOS clock generators.

Seven different fan-out variations, 1:2 to 1:12, are available. All of the devices are pin-compatible to each other for easy handling.

All family members share the same high performing characteristics such as low additive jitter, low skew, and wide operating temperature range.

The CDCLVC11xx supports an asynchronous output enable control (1G) which switches the outputs into a low state when 1G is low.

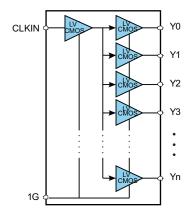
The CDCLVC11xx family operates in a 2.5-V and 3.3-V environment and are characterized for operation from -40°C to 85°C.

PART NUMBER	PACKAGE	BODY SIZE (NOM)						
CDCLVC1102								
CDCLVC1103	TSSOP (8)	3.00 mm × 4.40 mm						
CDCLVC1104								
CDCLVC1106	TSSOP (14)	5.00 mm × 4.40 mm						
CDCLVC1108	TSSOP (16)	5.00 mm x 4.40 mm						
CDCLVC1110	TSSOP (20)	6.50 mm × 4.40 mm						
CDCLVC1112	TSSOP (24)	7.80 mm × 4.40 mm						

#### Device Information<sup>(1)</sup>

(1) For all available packages, see the orderable addendum at the end of the data sheet.

#### **Functional Block Diagram**



CLKIN 1 24 Y	Y1
1G 2 CDCLVC 1102 23 Y	YЗ
	/DD
GND 4 CDCLVC 1104 21 Y	Y2
VDD 5 20 G	GND
Y4 6 CDCLVC 1106 19 Y	Y 5
GND 7 CDCLVC 1106 18 V	/DD
Y6 8 CDCLVC 1108 17 Y	Y7
	Y 8
Y9 10 CDCLVC 1110 15 G	GND
	Y 10
Y11 12 CDCLVC 1112 13 V	/DD



CDCLVC1106, CDCLVC1108, CDCLVC1110, CDCLVC1112

CDCLVC1102, CDCLVC1103, CDCLVC1104

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CI	hanges from Revision A (October 2014) to Revision B	Page
•	Changed Packaging name from TTSOP to TSSOP in Device Information Table	1
•	Changed CDCLVC1110 Y8 pin number from: 10 to: 12	3
•	Changed CDCLVC1110 Y9 pin number from: — to: 10	3
•	Moved T <sub>stg</sub> from ESD Ratings to Absolute Maximum Ratings	5
•	Added Receiving Notification of Documentation Updates and Community Resources sections	15

## Changes from Original (May 2010) to Revision A

Added ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section ......1



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Mechanical, Packaging, and Orderable

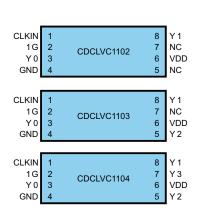
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## 5 Pin Configuration and Functions



		Top View		
CLKIN 1 G	1 2		14 13	Y 1 Y 3
Y0	2		13	VDD
GND	4	CDCLVC1106	11	Y 2
VDD	5		10	GND
Y 4	6		9	Y 5
GND	7		8	VDD
CLKIN	1		16	Y 1
1G	2		15	Y 3
Y 0	3		14	VDD
GND	4	CDCLVC1108	13	Y 2
VDD	5		12	GND
Y 4	6		11	Y 5
GND	7		10	VDD
Y 6	8		9	Υ7

PW Package 8-, 14-, 16-, 20, 24-Pin TSSOP

CLKIN 1G Y0 GND VDD Y4 GND Y6 VDD Y9	1 2 3 4 5 6 7 8 9 10	CDCLVC 1110	20 19 18 17 16 15 14 13 12 11	Y1 Y3 VDD Y2 GND Y5 VDD Y7 Y8 GND
	-			
CLKIN	1		24	Y1
1G	2		23	Y3
Y 0	3		22	VDD
GND	4		21	Y2
VDD	5		20	GND
Y 4	6	CDCLVC 1112	19	Y5
GND	7		18	VDD
Y 6	8		17	Y7
VDD	9		16	Y8
Y 9	10		15	GND
GND	11		14	Y 10
Y 11	12		13	VDD

#### **Pin Functions**

				PIN							
NAME	CDCLVC 1102	CDCLVC 1103	CDCLVC 1104	CDCLVC 1106	CDCLVC 1108	CDCLVC 1110	CDCLVC 1112	TYPE	DESCRIPTION		
LVCMC	VCMOS CLOCK INPUT										
CLKIN	1	1	1	1	1	1	1	Input	Input Pin		
CLOCK	CLOCK OUTPUT ENABLE										
1G	2	2	2	2	2	2	2	Input	Output Enable		
LVCMC	S CLOCK C	UTPUT									
Y0	3	3	3	3	3	3	3				
Y1	8	8	8	14	16	20	24				
Y2	_	5	5	11	13	17	21				
Y3	_	_	7	13	15	19	23				
Y4	_	_	_	6	6	6	6				
Y5	_	_	_	9	11	15	19	Quatraciat	LVCMOS output. Unused		
Y6	—	—	—	—	8	8	8	Output	outputs can be left floating.		
Y7	_	_	_	_	9	13	17				
Y8	_	_	_	_	_	12	16				
Y9	_	_	_	_	_	10	10				
Y10	_	_	_	_	_	—	14				
Y11	_	_	_	_	_	—	12				
SUPPL	Y VOLTAGE										
						5	5				
				5	5	Э	9	Power			
$V_{DD}$	6	6	6			9	13		2.5-V or device supply		
				8	10	14	18				
				12	14	18	22				
GROUM	ND										

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### **Pin Functions (continued)**

	PIN											
NAME	CDCLVC 1102	CDCLVC 1103	CDCLVC 1104	CDCLVC 1106	CDCLVC 1108	CDCLVC 1110	CDCLVC 1112	TYPE	DESCRIPTION			
							4					
				4	4	4	7					
GND	4	4 4	4	4	4	4			7	7 11 GND Device ground	GND	Device ground
				7	7	11	15					
		1	10	12	16	20						



### 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) <sup>(1)</sup>

		MIN	MAX	UNIT
$V_{DD}$	Supply voltage	-0.5	4.6	V
V <sub>IN</sub>	Input voltage <sup>(2)</sup>	-0.5	V <sub>DD</sub> + 0.5	V
Vo	Output voltage <sup>(2)</sup>	-0.5	V <sub>DD</sub> + 0.5	V
I <sub>IN</sub>	Input current	-20	20	mA
I <sub>O</sub>	Continuous output current	-50	50	mA
TJ	Maximum junction temperature		125	°C
T <sub>stg</sub>	Storage temperature	-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) This value is limited to 4.6 V maximum.

### 6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatio discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>		N/
V <sub>(ESD)</sub>	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1500	v

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V	0 I II	3.3-V supply	3.0	3.3	3.6	V
V <sub>DD</sub>	Supply voltage	2.5-V supply	2.3	2.5	2.7	v
V		$V_{DD} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$			V <sub>DD</sub> /2 - 600	mV
VIL	Low-level input voltage	$V_{DD} = 2.3 \text{ V to } 2.7 \text{ V}$			$V_{DD}/2 - 400$	mv
V	/ <sub>IH</sub> High-level input voltage	$V_{DD} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	V <sub>DD</sub> /2 + 600			
VIH		$V_{DD} = 2.3 \text{ V to } 2.7 \text{ V}$	V <sub>DD</sub> /2 + 400			mV
V <sub>th</sub>	Input threshold voltage	V <sub>DD</sub> = 2.3 V to 3.6 V		V <sub>DD</sub> /2		mV
t <sub>r</sub> / t <sub>f</sub>	Input slew rate		1		4	V/ns
	Minimum pulse width at	V <sub>DD</sub> = 3.0 V to 3.6 V	1.8			
t <sub>w</sub>	CLKIN	$V_{DD} = 2.3 \text{ V to } 2.7 \text{ V}$	2.75			ns
	LVCMOS clock Input	V <sub>DD</sub> = 3.0 V to 3.6 V	DC		250	N 41 1-
f <sub>CLK</sub>	Frequency	V <sub>DD</sub> = 2.3 V to 2.7 V	DC		180	MHz
T <sub>A</sub>	Operating free-air tempera	ture	-40		85	°C

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### 6.4 Thermal Information

	THERMAL METRIC <sup>(1)</sup>	CDCLVC1102 CDCLVC1103 CDCLVC1104	CDCLVC1106	CDCLVC1108	CDCLVC11010	CDCLVC1112	UNIT	
			PW (TSSOP)					
		8 PINS	14 PINS	16 PINS	20 PINS	24 PINS		
$R_{\thetaJA}$	Junction-to-ambient thermal resistance <sup>(2)</sup>	149.4	112.6	108.4	83.0	87.9	°C/W	
R <sub>0JC(top)</sub>	Junction-to-case(top) thermal resistance <sup>(3)</sup>	69.4	48.0	33.6	32.3	26.5	°C/W	

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report.

The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as (2) specified in JESD51-7, in an environment described in JESD51-2a.

The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-(3) standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

### 6.5 Electrical Characteristics

Over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN <sup>-</sup>	TYP <sup>(1)</sup>	MAX	UNIT
OVEF	RALL PARAMETERS FOR ALL V	/ERSIONS			•	
	Static device current <sup>(2)</sup>	$1G = V_{DD}$ ; CLKIN = 0 V or $V_{DD}$ ; $I_O = 0$ mA; $V_{DD} = 3.6$ V		6	10	mA
I <sub>DD</sub>	Static device current	$1G = V_{DD}$ ; CLKIN = 0 V or $V_{DD}$ ; $I_0 = 0$ mA; $V_{DD} = 2.7$ V		3	6	
I <sub>PD</sub>	Power-down current	$1G = 0 \text{ V}; \text{ CLKIN} = 0 \text{ V or } \text{V}_{\text{DD}}; \text{ I}_{\text{O}} = 0 \text{ mA}; \text{ V}_{\text{DD}} = 3.6 \text{ V or } 2.7 \text{ V}$			60	μA
C	Power dissipation capacitance	V <sub>DD</sub> = 3.3 V; f = 10 MHz		6		pF
C <sub>PD</sub>	per output <sup>(3)</sup>	V <sub>DD</sub> = 2.5 V; f = 10 MHz		4.5		
	Input leakage current at 1G		8		8	
II.	Input leakage current at CLKIN	$V_{I} = 0 V \text{ or } V_{DD}, V_{DD} = 3.6 V \text{ or } 2.7 V$	25		25	μA
D		V <sub>DD</sub> = 3.3 V		45		Ω
R <sub>OUT</sub>	Output impedance	$V_{DD} = 2.5 V$		60		L
4	Output frequency	$V_{DD} = 3 V \text{ to } 3.6 V$	DC		250	MHz
f <sub>OUT</sub>	OUT Output frequency	$V_{DD} = 2.3 \text{ V to } 2.7 \text{ V}$	DC		180	
OUTF	PUT PARAMETERS FOR V <sub>DD</sub> = 3	.3 V ± 0.3 V				
		$V_{DD} = 3 \text{ V}, I_{OH} = -0.1 \text{ mA}$	2.9			
V <sub>OH</sub>	High-level output voltage	$V_{DD} = 3 \text{ V}, I_{OH} = -8 \text{ mA}$	2.5			V
		$V_{DD} = 3 \text{ V}, I_{OH} = -12 \text{ mA}$	2.2			
		V <sub>DD</sub> = 3 V, I <sub>OL</sub> = 0.1 mA			0.1	
$V_{OL}$	Low-level output voltage	$V_{DD} = 3 \text{ V}, \text{ I}_{OL} = 8 \text{ mA}$			0.5	V
		V <sub>DD</sub> = 3 V, I <sub>OL</sub> = 12 mA			0.8	
OUTF	PUT PARAMETERS FOR V <sub>DD</sub> = 2	2.5 V ± 0.2 V				
		V <sub>DD</sub> = 2.3 V, I <sub>OH</sub> = -0.1 mA	2.2			V
V <sub>OH</sub>	High-level output voltage	V <sub>DD</sub> = 2.3 V, I <sub>OH</sub> = -8 mA	1.7			V
V		V <sub>DD</sub> = 2.3 V, I <sub>OL</sub> = 0.1 mA			0.1	V
V <sub>OL</sub>	Low-level output voltage	V <sub>DD</sub> = 2.3 V, I <sub>OL</sub> = 8 mA			0.5	v

(1) All typical values are at respective nominal V<sub>DD</sub>. For switching characteristics, outputs are terminated to 50 Ω to V<sub>DD</sub>/2 (see Figure 3).

For dynamic I<sub>DD</sub> over frequency see and Figure 1. (2)

(3)This is the formula for the power dissipation calculation (see and the *Power Considerations* section).

 $P_{tot} = P_{stat} + P_{dyn} + P_{Cload} [W]$   $P_{stat} = V_{DD} \times I_{DD} [W]$   $P_{stat} = C_{DD} \times V_{DD} \times$ 

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$$P_{dyn} = C_{PD} \times V_{DD} 2 \times f [VV]$$

 $\mathsf{P}_{\mathsf{Cload}} = \mathsf{C}_{\mathsf{load}} \times \mathsf{V}_{\mathsf{DD}} 2 \times f \times \mathsf{n} \ [\mathsf{W}]$ n = Number of switching output pins EXAS STRUMENTS

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#### 6.6 Switching Characteristics

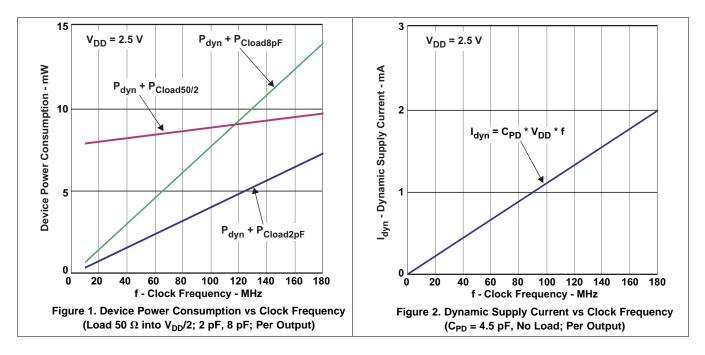
over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP MAX	UNIT
OUTPUT F	PARAMETERS FOR V <sub>DD</sub> = 3.3	V ± 0.3 V			
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation delay	CLKIN to Yn	0.8	2.0	ns
t <sub>sk(o)</sub>	Output skew	Equal load of each output		50	ps
t <sub>r</sub> /t <sub>f</sub>	Rise and fall time	20%–80% (V <sub>OH</sub> - V <sub>OL</sub> )	0.3	0.8	ns
t <sub>DIS</sub>	Output disable time	1G to Yn		6	ns
t <sub>EN</sub>	Output enable time	1G to Yn		6	ns
t <sub>sk(p)</sub>	Pulse skew ; $t_{PLH(Yn)} - t_{PHL(Yn)}$ <sup>(1)</sup>	To be measured with input duty cycle of 50%		180	ps
t <sub>sk(pp)</sub>	Part-to-part skew	Under equal operating conditions for two parts		0.5	ns
t <sub>jitter</sub>	Additive jitter rms <sup>(2)</sup>	12 kHz to 20 MHz, f <sub>OUT</sub> = 250 MHz		100	fs
OUTPUT F	PARAMETERS FOR V <sub>DD</sub> = 2.5	V ± 0.2 V		·	
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation delay	CLKIN to Yn	1	2.6	ns
t <sub>sk(o)</sub>	Output skew	Equal load of each output		50	ps
t <sub>r</sub> /t <sub>f</sub>	Rise and fall time	20%-80% reference point	0.3	1.2	ns
t <sub>DIS</sub>	Output disable time	1G to Yn		10	ns
t <sub>EN</sub>	Output enable time	1G to Yn		10	ns
t <sub>sk(p)</sub>	$ \begin{array}{l} \text{Pulse skew ;} \\ t_{\text{PLH}(Yn)} - t_{\text{PHL}(Yn)} \end{array} ^{(1)} \end{array} $	To be measured with input duty cycle of 50%		220	ps
t <sub>sk(pp)</sub>	Part-to-part skew	Under equal operating conditions for two parts		1.2	ns
t <sub>jitter</sub>	Additive jitter rms <sup>(2)</sup>	12 kHz to 20 MHz, f <sub>OUT</sub> = 180 MHz		350	fs

 $t_{sk(p)}$  depends on output rise- and fall-time  $(t_r/t_f)$ . The output duty-cycle can be calculated: odc =  $(t_{w(OUT)} \pm t_{sk(p)})/t_{period}$ ;  $t_{w(OUT)}$  is pulse-width of output waveform and tperiod is  $1/f_{OUT}$ . Parameter is specified by characterization. Not tested in production. (1)

(2)

### 6.7 Typical Characteristics



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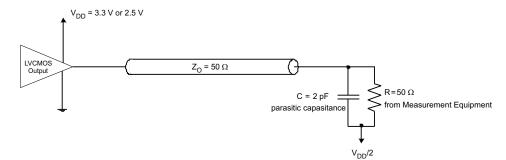
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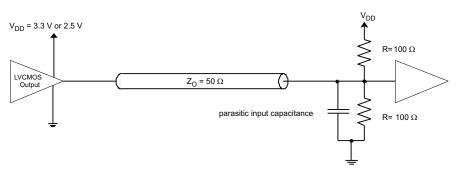
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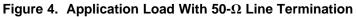


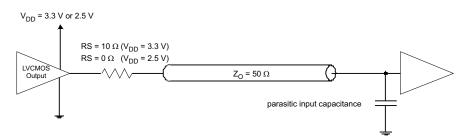
### 7 Parameter Measurement Information



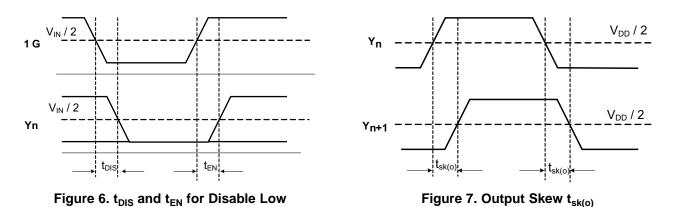








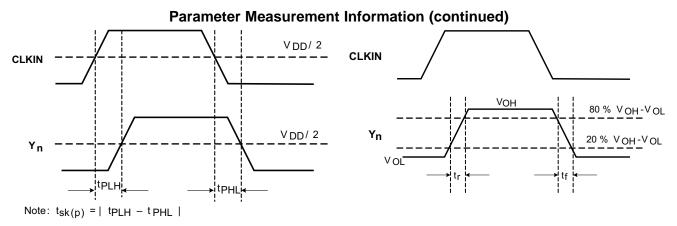


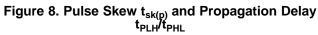


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### TEXAS INSTRUMENTS

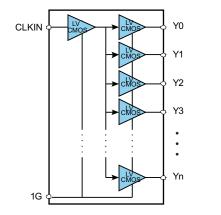
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### 8 Detailed Description

### 8.1 Overview

The CDCLVC11xx family of devices is a low-jitter and low-skew LVCMOS fan-out buffer solution. For best signal integrity, it is important to match the characteristic impedance of the CDCLVC11xx's output driver with that of the transmission line. Figure 5 and Figure 6 show the proper configuration per configuration for both  $V_{DD} = 3.3$  V and  $V_{DD} = 2.5$  V. TI recommends placing the series resistor close to the driver to minimize signal reflection.

### 8.2 Functional Block Diagram



1			24	Y1
2	CDCLVC	1102	23	Y3
3			22	VDD
4	CDCLVC	1104	21	Y2
5			20	GND
6	CDCUVC	1106	19	Y5
7	CDCLVC	1106	18	VDD
8	CDCLVC	1108	17	Y7
9			16	Y8
10	CDCLVC	1110	15	GND
11			14	Y 10
12	CDCLVC	1112	13	VDD
	2 3 4 5 6 7 8 9 10 11	2 CDCLVC 3 CDCLVC 4 CDCLVC 5 6 CDCLVC 7 CDCLVC 9 10 CDCLVC 11 CDCLVC	2 CDCLVC 1102 3 CDCLVC 1103 4 CDCLVC 1104 5 6 CDCLVC 1106 8 CDCLVC 1108 9 10 CDCLVC 1110 11 0 CDCLVC 1110	$\begin{array}{cccccccccccccccccccccccccccccccccccc$

#### Table 1. Output Logic Table

INP	OUTPUTS	
CLKIN	1G	Yn
Х	L	L
L	Н	L
Н	Н	Н

### 8.3 Feature Description

The outputs of the CDCLVC11xx can be disabled by driving the asynchronous output enable pin (1G) low. Unused output can be left floating to reduce overall system component cost. All supply and ground pins must be connected to  $V_{DD}$  and GND, respectively.

### 8.4 Device Functional Modes

The CDCLVC11xx operates from supplies between 2.5 V and 3.3 V.



9

Application and Implementation

#### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 9.1 Application Information

The CDCLVC11xx family is a low additive jitter LVCMOS buffer solution that can operate up to 250 MHz at and 180 MHz at  $V_{DD}$  = 2.5 V. Low output skew as well as the ability for asynchronous output enable is featured to simultaneously enable or disable buffered clock outputs as necessary in the application.

### 9.2 Typical Application

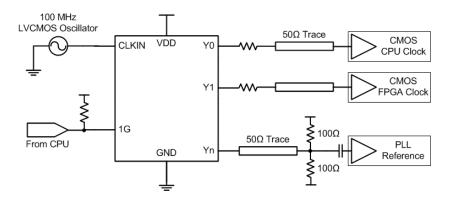


Figure 10. Example System Configuration

### 9.2.1 Design Requirements

The CDCLVC11xx shown in Figure 10 is configured to fan out a 100-MHz signal from a local LVCMOS oscillator. The CPU is configured to control the output state through 1G.

The configuration example is driving three LVCMOS receivers in a backplane application with the following properties:

- The CPU clock can accept a full swing DC-coupled LVCMOS signal. A series resistor is placed near the CDCLVC11xx to closely match the characteristic impedance of the trace to minimize reflections.
- The FPGA clock is similarly DC-coupled with an appropriate series resistor placed near the CDCLVC11xx.
- The PLL in this example can accept a lower amplitude signal, so a Thevenin's equivalent termination is used. The PLL receiver features internal biasing, so AC coupling can be used when common-mode voltage is mismatched.

### 9.2.2 Detailed Design Procedure

Refer to Figure 5 and the *Electrical Characteristics* table to determine the appropriate series resistance needed for matching the output impedance of the CDCLVC11xx to that of the characteristic impedance of the transmission line.

Unused outputs can be left floating. See the *Power Supply Recommendations* section for recommended filtering techniques.

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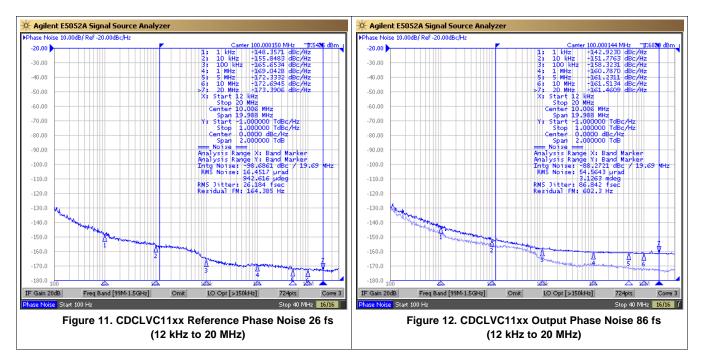
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### Typical Application (continued)

#### 9.2.3 Application Curves



The low additive jitter of the CDCLVC11xx can be shown in the previous application example. The low-noise 100-MHz XO with 26-fs RMS jitter drives the CDCLVC11xx, resulting in 86-fs RMS jitter when integrated from 12 kHz to 20 MHz. The resultant additive jitter is a low 82-fs RMS for this configuration.

### **10** Power Supply Recommendations

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12

High-performance clock buffers are sensitive to noise on the power supply, which can dramatically increase the additive jitter of the buffer. Thus, it is essential to reduce noise from the system power supply, especially when the jitter and phase noise is critical to applications.

Filter capacitors are used to eliminate the low-frequency noise from the power supply, where the bypass capacitors provide the very low impedance path for high-frequency noise and guards the power supply system against induced fluctuations. These bypass capacitors also provide instantaneous current surges as required by the device and should have low equivalent series resistance (ESR). To properly use the bypass capacitors, they must be placed very close to the power-supply terminals and laid out with short loops to minimize inductance. TI recommends adding as many high-frequency (for example, 0.1  $\mu$ F) bypass capacitors, as there are supply terminals in the package. TI recommends, but does not require, inserting a ferrite bead between the board power supply and the chip power supply that isolates the high-frequency switching noises generated by the clock buffer; these beads prevent the switching noise from leaking into the board supply. It is imperative to choose an appropriate ferrite bead with very low DC resistance to provide adequate isolation between the board supply and the chip supply, as well as to maintain a voltage at the supply terminals that is greater than the minimum voltage required for proper operation.

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### CDCLVC1102, CDCLVC1103, CDCLVC1104 CDCLVC1106, CDCLVC1108, CDCLVC1110, CDCLVC1112

SCAS895B-MAY 2010-REVISED FEBRUARY 2017

Figure 13 shows this recommended power supply decoupling method.

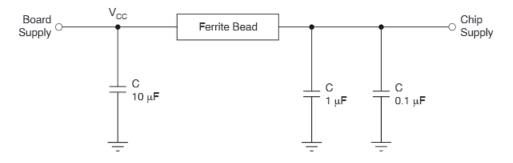


Figure 13. Power Supply Decoupling

### **10.1** Power Considerations

The following power consideration refers to the device-consumed power consumption only. The device power consumption is the sum of static power and dynamic power. The dynamic power usage consists of two components:

- Power used by the device as it switches states.
- Power required to charge any output load.

The output load can be capacitive only or capacitive and resistive. The following formula and the power graphs in and Figure 1 can be used to obtain the power consumption of the device:

$$\begin{split} & \mathsf{P}_{dev} = \mathsf{P}_{stat} + n \; (\mathsf{P}_{dyn} + \mathsf{P}_{Cload}) \\ & \mathsf{P}_{stat} = \mathsf{V}_{DD} \times \mathsf{I}_{DD} \\ & \mathsf{P}_{dyn} + \mathsf{P}_{Cload} = \text{see and Figure 1} \end{split}$$

where:

 $V_{DD}$  = Supply voltage ( or 2.5 V)

 $I_{DD}$  = Static device current (typical 6 mA for  $V_{DD}$  = 3.3 V; typical 3 mA for  $V_{DD}$  = 2.5 V)

n = Number of switching output pins

Example for device power consumption for CDCLVC1104: four outputs are switching, f = 120 MHz,  $V_{DD}$  = 3.3 V, and  $C_{load}$  = 2 pF per output:

 $P_{dev} = P_{stat} + n (P_{dyn} + P_{Cload}) = 19.8 \text{ mW} + 40 \text{ mW} = 59.8 \text{ mW} \\ P_{stat} = V_{DD} \times I_{DD} = 6 \text{ mA} \times 3.3 \text{ V} = 19.8 \text{ mW} \\ n (P_{dyn} + P_{Cload}) = 4 \times 10 \text{ mW} = 40 \text{ mW}$ 

### NOTE

For dimensioning the power supply, the total power consumption must be considered. The total power consumption is the sum of the device power consumption and the power consumption of the load.

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### 11 Layout

### 11.1 Layout Guidelines

Figure 14 shows a conceptual layout detailing recommended placement of power supply bypass capacitors. For component side mounting, use 0402 body size capacitors to facilitate signal routing. Keep the connections between the bypass capacitors and the power supply on the device as short as possible. Ground the other side of the capacitor using a low-impedance connection to the ground plane.

### 11.2 Layout Example

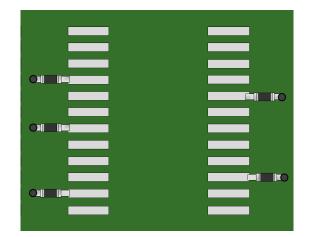


Figure 14. PCB Conceptual Layout



### **12 Device and Documentation Support**

#### 12.1 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
CDCLVC1102	Click here	Click here	Click here	Click here	Click here
CDCLVC1103	Click here	Click here	Click here	Click here	Click here
CDCLVC1104	Click here	Click here	Click here	Click here	Click here
CDCLVC1106	Click here	Click here	Click here	Click here	Click here
CDCLVC1108	Click here	Click here	Click here	Click here	Click here
CDCLVC1110	Click here	Click here	Click here	Click here	Click here
CDCLVC1112	Click here	Click here	Click here	Click here	Click here

#### Table 2. Related Links

### 12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### **12.3 Community Resources**

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E<sup>™</sup> Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support TI's Design Support** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 12.4 Trademarks

E2E is a trademark of Texas Instruments. All other trademarks are the property of their respective owners.

#### 12.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### 12.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

### 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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10-Dec-2020

### PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
	(1)		J			(2)	(6)	(0)		(40)	
CDCLVC1102PW	ACTIVE	TSSOP	PW	8	150	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C2	Samples
CDCLVC1102PWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C2	Samples
CDCLVC1103PW	ACTIVE	TSSOP	PW	8	150	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C3	Samples
CDCLVC1103PWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C3	Samples
CDCLVC1104PW	ACTIVE	TSSOP	PW	8	150	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C4	Samples
CDCLVC1104PWR	ACTIVE	TSSOP	PW	8	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C4	Samples
CDCLVC1106PW	ACTIVE	TSSOP	PW	14	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C6	Samples
CDCLVC1106PWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C6	Samples
CDCLVC1108PW	ACTIVE	TSSOP	PW	16	90	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C8	Samples
CDCLVC1108PWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9C8	Samples
CDCLVC1110PW	ACTIVE	TSSOP	PW	20	70	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9CA	Samples
CDCLVC1110PWR	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9CA	Samples
CDCLVC1112PW	ACTIVE	TSSOP	PW	24	60	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9CC	Samples
CDCLVC1112PWR	ACTIVE	TSSOP	PW	24	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	C9CC	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW**: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".



## PACKAGE OPTION ADDENDUM

10-Dec-2020

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption. **Green:** TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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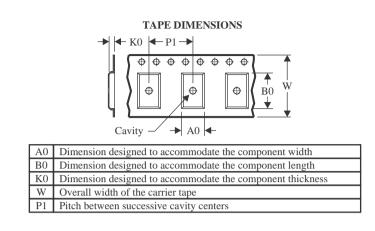


Texas

STRUMENTS

### TAPE AND REEL INFORMATION





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CDCLVC1102PWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
CDCLVC1103PWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
CDCLVC1104PWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
CDCLVC1106PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
CDCLVC1110PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
CDCLVC1112PWR	TSSOP	PW	24	2000	330.0	16.4	6.95	8.3	1.6	8.0	16.0	Q1



## PACKAGE MATERIALS INFORMATION

2-Oct-2024



All ulmensions are normal							r.	
Device	evice Package Type		Package Type Package Drawing Pins SPC		SPQ	Length (mm)	Width (mm)	Height (mm)
CDCLVC1102PWR	TSSOP	PW	8	2000	356.0	356.0	35.0	
CDCLVC1103PWR	TSSOP	PW	8	2000	367.0	367.0	35.0	
CDCLVC1104PWR	TSSOP	PW	8	2000	367.0	367.0	35.0	
CDCLVC1106PWR	TSSOP	PW	14	2000	367.0	367.0	35.0	
CDCLVC1110PWR	TSSOP	PW	20	2000	356.0	356.0	35.0	
CDCLVC1112PWR	TSSOP	PW	24	2000	356.0	356.0	35.0	

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2-Oct-2024

### TUBE



## - B - Alignment groove width

#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
CDCLVC1102PW	PW	TSSOP	8	150	530	10.2	3600	3.5
CDCLVC1103PW	PW	TSSOP	8	150	530	10.2	3600	3.5
CDCLVC1104PW	PW	TSSOP	8	150	530	10.2	3600	3.5
CDCLVC1106PW	PW	TSSOP	14	90	530	10.2	3600	3.5
CDCLVC1108PW	PW	TSSOP	16	90	530	10.2	3600	3.5
CDCLVC1110PW	PW	TSSOP	20	70	530	10.2	3600	3.5
CDCLVC1112PW	PW	TSSOP	24	60	530	10.2	3600	3.5

# **PW0014A**



## **PACKAGE OUTLINE**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



## PW0014A

# **EXAMPLE BOARD LAYOUT**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



## PW0014A

## **EXAMPLE STENCIL DESIGN**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



## **PW0008A**



## **PACKAGE OUTLINE**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153, variation AA.



## PW0008A

# **EXAMPLE BOARD LAYOUT**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



## PW0008A

# **EXAMPLE STENCIL DESIGN**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

9. Board assembly site may have different recommendations for stencil design.



<sup>8.</sup> Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

## **PW0020A**



## **PACKAGE OUTLINE**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



## PW0020A

# **EXAMPLE BOARD LAYOUT**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



## PW0020A

## **EXAMPLE STENCIL DESIGN**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



# **PW0016A**



## **PACKAGE OUTLINE**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



## PW0016A

# **EXAMPLE BOARD LAYOUT**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



## PW0016A

## **EXAMPLE STENCIL DESIGN**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

9. Board assembly site may have different recommendations for stencil design.



<sup>8.</sup> Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

## **PW0024A**



## **PACKAGE OUTLINE**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



## PW0024A

# **EXAMPLE BOARD LAYOUT**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



## PW0024A

## **EXAMPLE STENCIL DESIGN**

## TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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